Optical Processes In Semiconductors Pankove

For some time there has been a need for a semiconductor device book that carries diode and transistor theory beyond an introductory level and yet has space to touch on a wider range of semiconductor device principles and applica tions. Such topics are covered in specialized monographs numbering many hun dreds, but the voluminous nature of this literature limits access for students. This book is the outcome of attempts to develop a broad course on devices and integrated electronics for university students at about senior-year level. The edu cational prerequisites are an introductory course in semiconductor junction and transistor concepts, and a course on analog and digital circuits that has intro duced the concepts of rectification, amplification, oscillators, modulation and logic and SWitching circuits. The book should also be of value to professional engineers and physicists because of both, the information included and the de tailed guide to the literature given by the references. The aim has been to bring some measure of order into the subject area examined and to provide a basic structure from which teachers may develop themes that are of most interest to students and themselves. Semiconductor devices and integrated circuits are reviewed and fundamental factors that control power levels, frequency, speed, size and cost are discussed. The text also briefly mentions how devices are used and presents circuits and comments on representative applications. Thus, the book seeks a balance be tween the extremes of device physics and circuit design.

Introduction to Econometrics provides a step by step introductory guide to the core areas of this subject.This new edition of Dougherty's highly successful textbook has been substantially updated and revised with the inclusion of new material on specification tests, binary choice models, tobit analysis, sample selection bias, nonstationary time series, and unit root tests and cointegration. In addition, the book will be acompanied by a website containing graphical treatment of allthe topics covered in the text.

"The most striking feature of the book is its modern outlookprovides a wonderful foundation. The most wonderful feature is its efficient style of expositionan excellent book." PHYSICS TODAY "There is nothing quite like itThose embarking on research into the optical properties of semiconductors will benefit from working through these chaptersa solid introduction to the optical properties of semiconductors" CONTEMPORARY PHYSICS

The theoretical basis and the relevant experimental knowledge underlying our present understanding of the electrical and optical properties of semiconductor heterostructures. Although such structures have been known since the 1940s, it was only in the 1980s that they moved to the forefront of research. The resulting structures have remarkable properties not shared by bulk materials. The text begins with a description of the electronic properties of various types of heterostructures, including discussions of complex band-structure effects, localised states, tunnelling phenomena, and excitonic states. The focus of the remainder of the book is on optical properties, including intraband absorption, luminescence and recombination, Raman scattering, subband optical transitions, nonlinear effects, and ultrafast optical phenomena. The concluding chapter presents an overview of some of the applications that make use of the physics discussed. Appendices provide background information on band structure theory, kinetic theory, electromagnetic modes, and Coulomb effects.

A large number of solar cell and solar cell systems are described in this volume. The theory of their operation, their design and the levels of their performance is discussed. Originally the book appeared in 1978 but extensive change over the intervening years in the fields of energy generation and consumption, solar energy and solar cells, has necessitated the publication of an updated version. The text initially surveys

the requirements of humanity, the subsequent need for solar cells, the nature of sunlight and the properties of semiconductors. Concrete examples, extensive references and theoretical arguments are then used to present a comparison of options available in the design and operation of solar cells and solar cell systems. The cells - constructed from single, crystal, polycrystalline and amorphous semiconductors - and the systems - have varying designs and differing levels of solar energy for input and produce electricity or electrical and thermal energies. Solar cell production, economics and environmental effects are considered throughout the publication.

This is the 22nd Volume in the series Memorial Tributes compiled by the National Academy of Engineering as a personal remembrance of the lives and outstanding achievements of its members and foreign associates. These volumes are intended to stand as an enduring record of the many contributions of engineers and engineering to the benefit of humankind. In most cases, the authors of the tributes are contemporaries or colleagues who had personal knowledge of the interests and the engineering accomplishments of the deceased. Through its members and foreign associates, the Academy carries out the responsibilities for which it was established in 1964. Under the charter of the National Academy of Sciences, the National Academy of Engineering was formed as a parallel organization of outstanding engineers. Members are elected on the basis of significant contributions to engineering theory and practice and to the literature of engineering or on the basis of demonstrated unusual accomplishments in the pioneering of new and developing fields of technology. The National Academies share a responsibility to advise the federal government on matters of science and technology. The expertise and credibility that the National Academy of Engineering brings to that task stem directly from the abilities, interests, and achievements of our members and foreign associates, our colleagues and friends, whose special gifts we remember in this book.

Microcharacterization of materials is a rapidly advancing field. Among the many electron and ion probe techniques, the cathodoluminescence mode of an electron probe instrument has reached a certain maturity, which is reflected by an increas ing number of publications in this field. The rapid rate of progress in applications of cathodoluminescence techniques in characterizing inorganic solids has been especially noticeable in recent years. The main purpose of the book is to outline the applications of cath odoluminescence techniques in the assessment of optical and electronic proper ties of inorganic solids, such as semiconductors, phosphors, ceramics, and min erals. The assessment provides, for example, information on impurity levels derived from cathodoluminescence spectroscopy, analysis of dopant concentra tions at a level that, in some cases, is several orders of magnitude lower than that attainable by x-ray microanalysis, the mapping of defects, and the determination of carrier lifetimes and the charge carrier capture cross sections of impurities. In order to make the book self-contained, some basic concepts of solid-state phys ics, as well as various cathodoluminescence techniques and the processes leading to luminescence phenomena in inorganic solids, are also described. We hope that this book will be useful to both scientists and graduate students interested in microcharacterization of inorganic solids. This book, however, was not intended as a definitive account of cathodoluminescence analysis of in organic solids. In considering the results presented here, readers should re member that many materials have properties that vary widely as a function of preparation conditions.

This is the third volume of the very successful set. This updated volume will contain non-linear properties of some of the most useful materials as well as chapters on optical measurement techniques. * Contributors have decided the best values for n and k * References in each critique allow the reader to go back to the original data to examine and understand where the values have come from * Allows the reader to determine if any data in a spectral region needs to be filled in * Gives a wide and detailed view of

experimental techniques for measuring the optical constants n and k * Incorporates and describes crystal structure, space-group symmetry, unit-cell dimensions, number of optic and acoustic modes, frequencies of optic modes, the irreducible representation, band gap, plasma frequency, and static dielectric constant

Characterization of Semiconductor Heterostructures and Nanostructures is structured so that each chapter is devoted to a specific characterization technique used in the understanding of the properties (structural, physical, chemical, electrical etc..) of semiconductor quantum wells and superlattices. An additional chapter is devoted to ab initio modeling. The book has two basic aims. The first is educational, providing the basic concepts of each of the selected techniques with an approach understandable by advanced students in Physics, Chemistry, Material Science, Engineering, Nanotechnology. The second aim is to provide a selected set of examples from the recent literature of the TOP results obtained with the specific technique in understanding the properties of semiconductor heterostructures and nanostructures. Each chapter has this double structure: the first part devoted to explain the basic concepts, and the second to the discussion of the most peculiar and innovative examples. The topic of quantum wells, wires and dots should be seen as a pretext of applying top level characterization techniques in understanding the structural, electronic etc properties of matter at the nanometer (and even sub-nanometer) scale. In this respect it is an essential reference in the much broader, and extremely hot, field of Nanotechnology. Comprehensive collection of the most powerful characterization techniques for semiconductors heterostructures and nanostructures Most of the chapters are authored by scientists that are world-wide among the top-ten in publication ranking of the specific field Each chapter starts with a didactic introduction on the technique The second part of each chapters deals with a selection of top examples highlighting the power of the specific technique to analyse the properties of semiconductors heterostructures and nanostructures

Comprehensive text and reference covers all phenomena involving light in semiconductors, emphasizing modern applications in semiconductor lasers, electroluminescence, photodetectors, photoconductors, photoemitters, polarization effects, absorption spectroscopy, more. Numerous problems. 339 illustrations.

Optical Processes in SemiconductorsCourier Corporation

Following a semi-quantitative approach, this book presents a summary of the basic concepts, with examples and applications, and reviews recent developments in the study of optical properties of condensed matter systems. Key Features: Covers basic knowledge as well as application topics Includes theory, experimental techniques and current and developing applications Timely and useful contribution to the literature Written by internationally respected contributors working in physics and electrical engineering departments and government laboratories

This graduate text explains the physical properties and applications of a wide range of smart materials.

This book describes the intrinsic optical processes occurring in semiconductor bulk and engineered semiconductor structures such as quantum wells, quantum wires, quantum dots, and superlattices. The topic has gained attention as all optoelectronic devices used in fibre-optic communication and optical computers are made of semiconductors and their engineered structures.

In introductory solid-state physics texts we are introduced to the concept of a perfect crystalline solid with every atom in its proper place. This is a convenient first step in developing the concept of electronic band struc ture, and from it deducing the general electronic and optical properties of crystalline solids. However, for the student who does not proceed further, such an idealization can be grossly misleading. A perfect crystal does not exist. There are always defects. It was recognized very early in the study of solids that these defects often have a profound effect on the real physical properties of a solid. As a result, a major part of scientific research in solid-state physics has,' from the early studies of "color centers" in alkali halides to the present vigorous investigations of deep levels in semiconductors, been devoted to the study of defects. We now know that in actual fact, most of the interest ing and important properties of solids-electrical, optical, mechanical-are determined not so much by the properties of the perfect crystal as by its im perfections.

Optical Materials, Second Edition, presents, in a unified form, the underlying physical and structural processes that determine the optical behavior of materials. It does this by combining elements from physics, optics, and materials science in a seamless manner, and introducing quantum mechanics when needed. The book groups the characteristics of optical materials into classes with similar behavior. In treating each type of material, the text pays particular attention to atomic composition and chemical makeup, electronic states and band structure, and physical microstructure so that the reader will gain insight into the kinds of materials engineering and processing conditions that are required to produce a material exhibiting a desired optical property. The physical principles are presented on many levels, including a physical explanation, followed by formal mathematical support and examples and methods of measurement. The reader may overlook the equations with no loss of comprehension, or may use the text to find appropriate equations for calculations of optical properties. Includes a fundamental description of optical materials at the beginner and advanced levels Provides a thorough coverage of the field and presents new concepts in an easy to understand manner that combines written explanations and equations Serves as a valuable toolbox of applications and equations for the working reader

This set of five volumes, four volumes edited by Edward D. Palik and a volume by Gorachand Ghosh, is a unique resource for any science and technology library. It provides materials researchers and optical device designers with reference facts in a context not available anywhere else. The singular functionality of the set derives from the unique format for the three core volumes that comprise the Handbook of Optical Constants of Solids. The Handbook satisfies several essential needs: first, it affords the most comprehensive database of the refractive index and extinction (or loss) coefficient of technically important and scientifically interesting dielectrics. This data has been critically selected and evaluated by authorities on each material. Second, the dielectric constant database is supplemented by tutorial chapters covering the basics of dielectric theory and reviews of experimental techniques for each wavelength region and material characteristic. As an additional resource, two of the tutorial chapters summarize the relevant characteristics of each of the materials in the database. The data in the core volumes have been collected and analyzed over a period of twelve years, with the most recent completed in 1997. The volumes systematically define the dielectric properties of 143 of the most engaging materials, including metals, semiconductors, and insulators. Together, the three Palik books contain nearly 3,000 pages, with about 2/3 devoted to the dielectric constant data. The tutorial chapters in the remaining 1/3 of the pages contain a wealth of information, including some dielectric data. Hence, the separate volume, Index to Handbook of Optical Constants of Solids, which is included as part of the set, substantially enhances the utility of the Handbook and in essence, joins all the Palik volumes into one unit. It isthen of great importance to users of the set. A final volume rounds out the set. The Handbook of Thermo-Optic Coefficients of Optical Materials with Applications collects refractive index measurements and their temperature dependence for a large number of

crystals and glasses. Mathematical models represent these data, and in turn are used in the design of nonlinear optical devices. * Unique source of extremely useful optical data for a very broad community of scientists, researchers, and practitioners * Will be of great practical applicability to both industry and research * Presents optical constants for a broadest spectral range, for a very large number of materials: Paliks three volumes include 143 materials including 43 elements; Ghoshs volume includes some 70 technologically interesting crystals and many commercial glasses * Includes a special index volume that enables the user to search for the information in the three Palik volumes easily and quickly * Critique chapters in the Palik volumes discuss the data and give reference to most of the literature available for each material * Presents various techniques for measuring the optical constants and mathematical models for analytical calculations of some data

In addition to the topics discussed in the First Edition, this Second Edition contains introductory treatments of superconducting materials and of ferromagnetism. I think the book is now more balanced because it is divided perhaps 60% - 40% between devices (of all kinds) and materials (of all kinds). For the physicist interested in solid state applications, I suggest that this ratio is reasonable. I have also rewritten a number of sections in the interest of (hopefully) increased clarity. The aims remain those stated in the Preface to the First Edition; the book is a survey of the physics of a number of solid state devices and ma terials. Since my object is a discussion of the basic ideas in a number of fields, I have not tried to present the "state of the art," especially in semi conductor devices. Applied solid state physics is too vast and rapidly changing to cover completely, and there are many references available to recent developments. For these reasons, I have not treated a number of interesting areas. Among the lacunae are superiattices, heterostructures, compound semiconductor devices, ballistic transistors, integrated optics, and light wave communications. (Suggested references to those subjects are given in an appendix.) I have tried to cover some of the recent revolutionary developments in superconducting materials.

This textbook presents the basic elements needed to understand and engage in research in semiconductor physics. It deals with elementary excitations in bulk and low-dimensional semiconductors, including quantum wells, quantum wires and quantum dots. The basic principles underlying optical nonlinearities are developed, including excitonic and many-body plasma effects. The fundamentals of optical bistability, semiconductor lasers, femtosecond excitation, optical Stark effect, semiconductor photon echo, magneto-optic effects, as well as bulk and quantum-confined Franz-Keldysh effects are covered. The material is presented in sufficient detail for graduate students and researchers who have a general background in quantum mechanics.

This revised and updated edition of the well-received book by C. Klingshirn provides an introduction to and an overview of all aspects of semiconductor optics, from IR to visible and UV. It has been split into two volumes and rearranged to offer a clearer structure of the course content. Inserts on important experimental techniques as well as sections on topical research have been added to support research-oriented teaching and learning. Volume 1 provides an introduction to the linear optical properties of semiconductors. The mathematical treatment has been kept as elementary as possible to allow an intuitive approach to the understanding of results of semiconductor spectroscopy. Building on the phenomenological model of the Lorentz oscillator, the book describes the interaction of light with fundamental optical excitations in semiconductors (phonons, free carriers, excitons). It also offers a broad review of seminal research results augmented by concise descriptions of the relevant experimental techniques, e.g., Fourier transform IR spectroscopy, ellipsometry, modulation spectroscopy and spatially resolved methods, to name a few. Further, it picks up on hot topics in current research, like quantum structures, mono-layer semiconductors or Perovskites. The experimental aspects of semiconductor optics are complemented by an in-depth discussion of group theory in solid-state optics. Covering subjects ranging from physics to materials science and optoelectronics, this book provides a lively and

comprehensive introduction to semiconductor optics. With over 120 problems, more than 480 figures, abstracts to each chapter, as well as boxed inserts and a detailed index, it is intended for use in graduate courses in physics and neighboring sciences like material science and electrical engineering. It is also a valuable reference resource for doctoral and advanced researchers.

This book covers a broad spectrum of the silicon-based materials and their device applications. This book provides a broad coverage of the silicon-based materials including different kinds of silicon-related materials, their processing, spectroscopic characterization, physical properties, and device applications. This two-volume set offers a selection of timely topics on silicon materials namely those that have been extensively used for applications in electronic and photonic technologies. The extensive reference provides broad coverage of silicon-based materials, including different types of silicon-related materials, their processing, spectroscopic characterization, physical properties, and device applications. Fourteen chapters review the state of the art research on silicon-based materials and their applications to devices. This reference contains a subset of articles published in AP's recently released Handbook of Advanced Electronic and Photonic Materials and Devices (2000, ISBN 012-5137451, ten volumes) by Dr. Hari Nalwa. This two-volume work strives to present a highly coherent coverage of silicon-based material uses in the vastly dynamic arena of silicon chip research and technology. Key Features * Covers silicon-based materials and devices * Include types of materials, their processing, fabrication, physical properties and device applications * Role of silicon-based materials in electronic and photonic technology * A very special topic presented in a timely manner and in a format

This book traces the history of the concept of work from its earliest stages and shows that its further formalization leads to equilibrium principle and to the principle of virtual works, and so pointing the way ahead for future research and applications. The idea that something remains constant in a machine operation is very old and has been expressed by many mathematicians and philosophers such as, for instance, Aristotle. Thus, a concept of energy developed. Another important idea in machine operation is Archimedes' lever principle. In modern times the concept of work is analyzed in the context of applied mechanics mainly in Lazare Carnot mechanics and the mechanics of the new generation of polytechnical engineers like Navier, Coriolis and Poncelet. In this context the word "work" is finally adopted. These engineers are also responsible for the incorporation of the concept of work into the discipline of economics when they endeavoured to combine the study of the work of machines and men together.

Bridging the gap between a general solid-state physics textbook and research articles, the renowned authors provide detailed explanations of the electronic, vibrational, transport, and optical properties of semiconductors. Their approach is a physical and intuitive one, rather than formal and pedantic. This textbook has been written with both students and researchers in mind, and the authors therefore present theories to explain experimental results. Throughout, the emphasis is on understanding the physical properties of Si, and similar tetrahedrally coordinated semiconductors, with explanations based on physical insights. Each chapter is enriched by an extensive collection of tables of material parameters, figures and problems -- many of the latter 'lead students by the hand' to arrive at the results.

Doping profiles are a key element in the development of modern semiconductor technology. This book is the first to give a comprehensive review of the theory, fabrication, characterization, and device applications of abrupt, shallow, and narrow doping profiles in semiconductors. After an introductory chapter sets out the basic theoretical and experimental concepts involved, the

authors discuss the fabrication of abrupt and narrow doping profiles by several different techniques, including epitaxial growth. They then present the techniques for characterizing doping distributions, followed by several chapters on the inherent physical properties of narrow doping profiles. The latter part of the book deals with specific devices. The book will be of great interest to graduate students, researchers, and engineers in the fields of semiconductor physics and microelectronic engineering.
Containing more than 300 equations and nearly 500 drawings, photographs, and micrographs, this reference surveys key areas such as optical measurements and in-line calibration methods. It describes cleanroom-based measurement technology used during the manufacture of silicon integrated circuits and covers model-based, critical dimension, overlay
Semiconducting and Insulating Crystals details how absorption spectroscopy provides information on the nature, concentration, charge state and configuration of impurities in crystals and also on their kinetics and transformations under annealing. After an introduction of the bulk optical properties of semiconductors and insulators and of impurities in crystals, this book presents the physical bases necessary for the understanding of impurity spectra. The description of various set-ups and accessories used in absorption spectroscopy is followed by a presentation of experimental results on specific impurities and classes of impurities and their relation with those obtained by various computation and by other experimental techniques.
Examines the optical properties of low-dimensional semiconductor structures, a hot research area - for graduate students and researchers.
Updated to reflect recent work in the field, this book emphasizes crystalline solids, going from the crystal lattice to the ideas of reciprocal space and Brillouin zones, and develops these ideas for lattice vibrations, for the theory of metals, and for semiconductors. The theme of lattice periodicity and its varied consequences runs through eighty percent of the book. Other sections deal with major aspects of solid state physics controlled by other phenomena: superconductivity, dielectric and magnetic properties, and magnetic resonance.
Semiconductors and Semimetals
The three volumes of this handbook treat the fundamentals, technology and nanotechnology of nitride semiconductors with an extraordinary clarity and depth. They present all the necessary basics of semiconductor and device physics and engineering together with an extensive reference section. Volume 2 addresses the electrical and optical properties of nitride materials. It includes semiconductor metal contacts, impurity and carrier concentrations, and carrier transport in semiconductors.
The monographic book addresses the basics of the charge carrier photoemission from one solid to another - the internal photoemission, (IPE) - and different spectroscopic applications of this phenomenon to solid state heterojunctions. This is the first book in the field of IPE, which complements the conventional external photoemission spectroscopy by analysing interfaces separated from the sample surface by a layer of a different solid or liquid. IPE is providing the most straightforward and, therefore, reliable information regarding the energy spectrum of electron states at interfaces. At the same time, the method provides the unique capability of analysing the heterostructures relevant to the modern micro- and nano-electronic devices as well as new

materials involved in their design and fabrication. In addition to the discussion of fundamental physical and technical aspects of IPE spectroscopic applications, several “hot topics are addressed. These include development of new insulating materials for advances Si MOS technology (both high-k gate insulators and low-k dielectrics for interconnect insulation), metal gate materials, development of heterostructures based on high-mobility semiconductors, etc. Thanks to a considerable activity in this field over the last few years, the recent results concerning band structure of most important interfaces involving novel materials can now be documented. - First complete description of the internal photoemission phenomena - A practical guide to internal photoemission measurements - Describes reliable energy barrier determination procedures - Surveys trap spectroscopy methods applicable to thin insulating layers - Provides an overview of the most recent results on band structure of high-permittivity insulating materials and their interfaces - Contains a complete collection of reference data on interface band alignment for wide-bandgap insulating materials in contact with metals and semiconductors

The second, updated edition of this essential reference book provides a wealth of detail on a wide range of electronic and photonic materials, starting from fundamentals and building up to advanced topics and applications. Its extensive coverage, with clear illustrations and applications, carefully selected chapter sequencing and logical flow, makes it very different from other electronic materials handbooks. It has been written by professionals in the field and instructors who teach the subject at a university or in corporate laboratories. The Springer Handbook of Electronic and Photonic Materials, second edition, includes practical applications used as examples, details of experimental techniques, useful tables that summarize equations, and, most importantly, properties of various materials, as well as an extensive glossary. Along with significant updates to the content and the references, the second edition includes a number of new chapters such as those covering novel materials and selected applications. This handbook is a valuable resource for graduate students, researchers and practicing professionals working in the area of electronic, optoelectronic and photonic materials.

This book gives a fascinating picture of the state-of-the-art in silicon photonics and a perspective on what can be expected in the near future. It is composed of a selected number of reviews authored by world leaders in the field and is written from both academic and industrial viewpoints. An in-depth discussion of the route towards fully integrated silicon photonics is presented. This book will be useful not only to physicists, chemists, materials scientists, and engineers but also to graduate students who are interested in the fields of microphotonics and optoelectronics.

Knowledge of the refractive indices and absorption coefficients of semiconductors is especially import in the design and analysis of optical and optoelectronic devices. The determination of the optical constants of semiconductors at energies beyond the fundamental absorption edge is also known to be a powerful way of studying the electronic energy-band structures of the semiconductors. The purpose of this book is to give tabulated values and graphical information on the optical constants of the most popular semiconductors over the entire spectral range. This book presents data on the optical constants of crystalline and amorphous semiconductors. A complete set of the optical constants are presented in this book. They are: the complex dielectric

constant (E=e.+ieJ, complex refractive index (n*=n+ik), absorption coefficient (a.), and normal-incidence reflectivity (R). The semiconductor materials considered in this book are the group-IV elemental and binary, lll-V, IT-VI, IV-VI binary semiconductors, and their alloys. The reader will fmd the companion book "Optical Properties of Crystalline and Amorphous Semiconductors: Materials and Fundamental Principles" useful since it emphasizes the basic material properties and fundamental prinCiples. Resistivity -- Carrier and doping density -- Contact resistance and Schottky barriers -- Series resistance, channel length and width, and threshold voltage -- Defects -- Oxide and interface trapped charges, oxide thickness -- Carrier lifetimes -- Mobility -- Charge-based and probe characterization -- Optical characterization -- Chemical and physical characterization -- Reliability and failure analysis.